

FIG. 1  
(PRIOR ART)

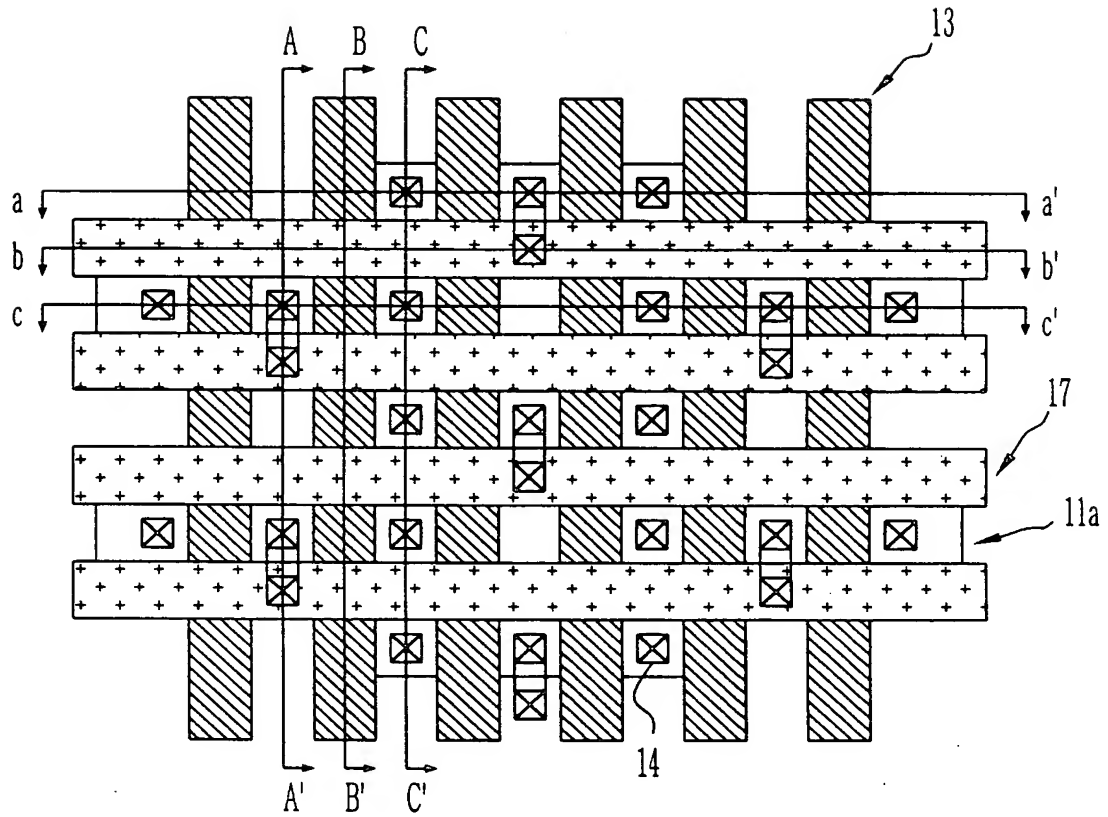


FIG. 2A  
(PRIOR ART)

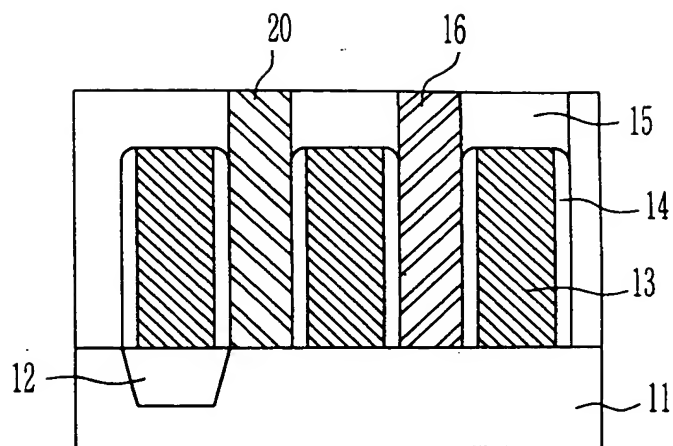


FIG. 2B  
(PRIOR ART)

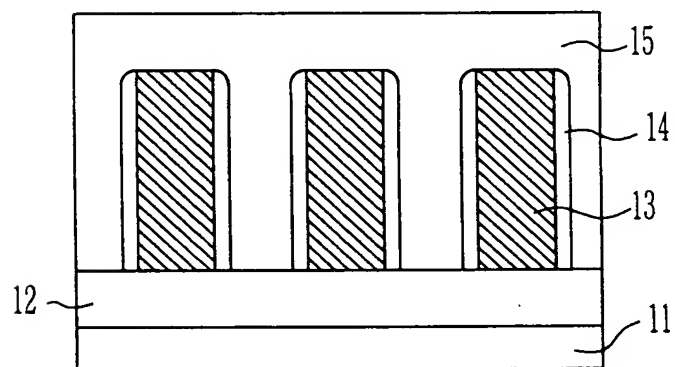


FIG. 2C  
(PRIOR ART)

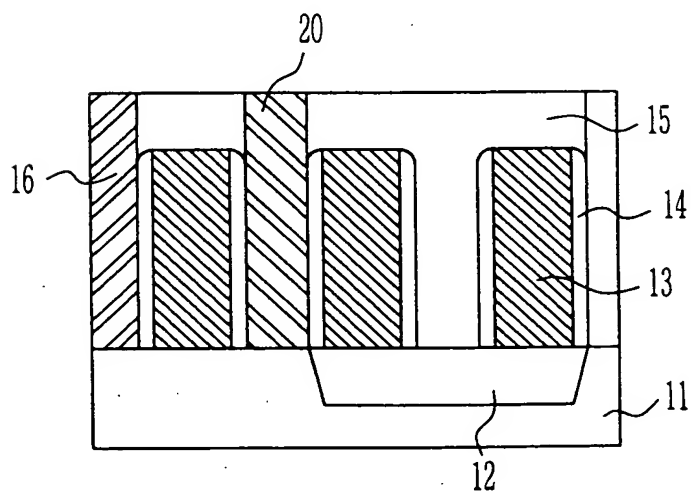


FIG. 3A  
(PRIOR ART)

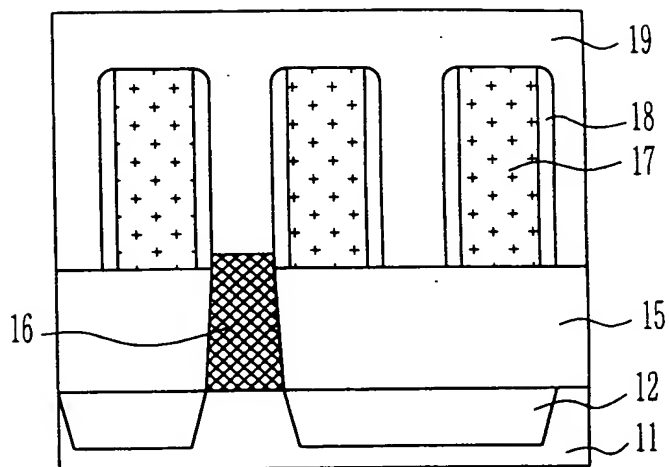


FIG. 3B  
(PRIOR ART)

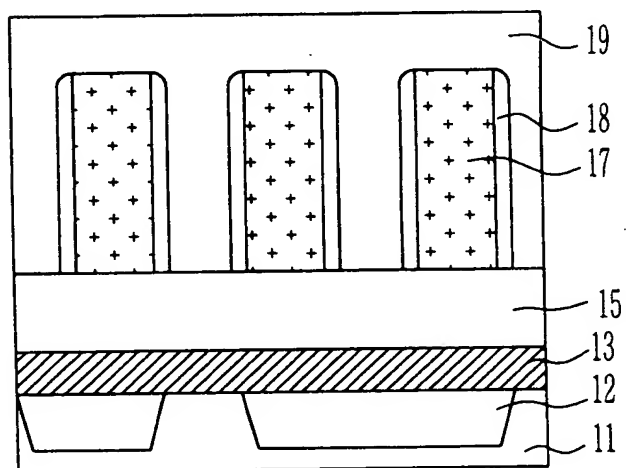


FIG. 3C  
(PRIOR ART)

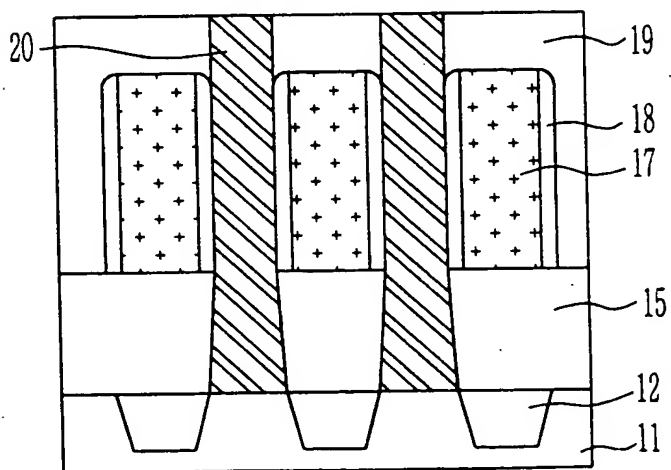


FIG. 4A  
(PRIOR ART)

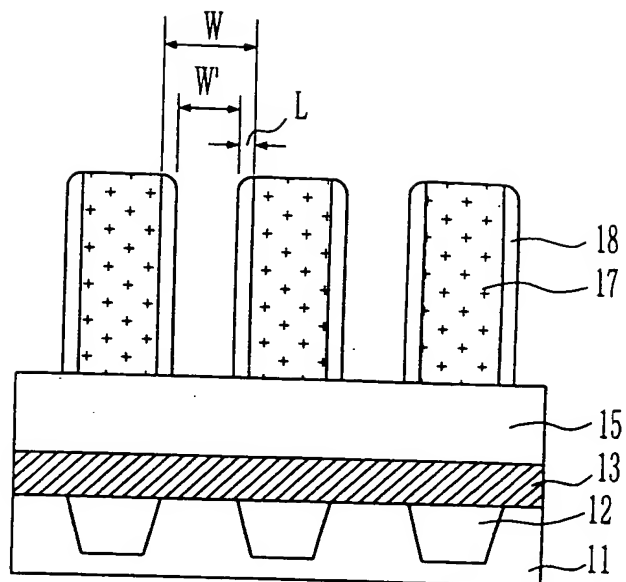


FIG. 4B  
(PRIOR ART)

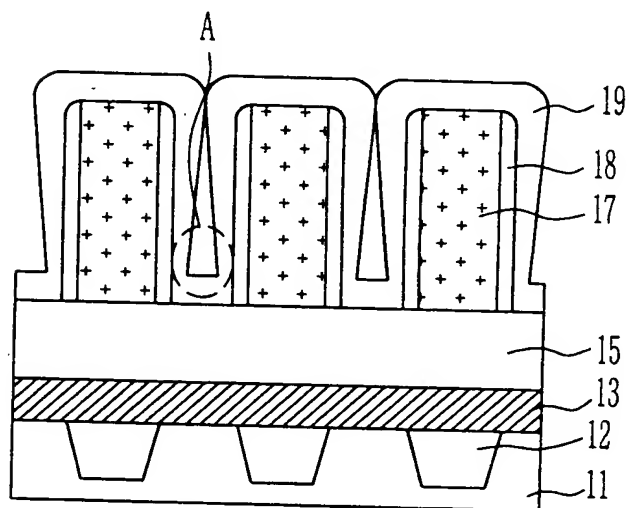


FIG. 5A

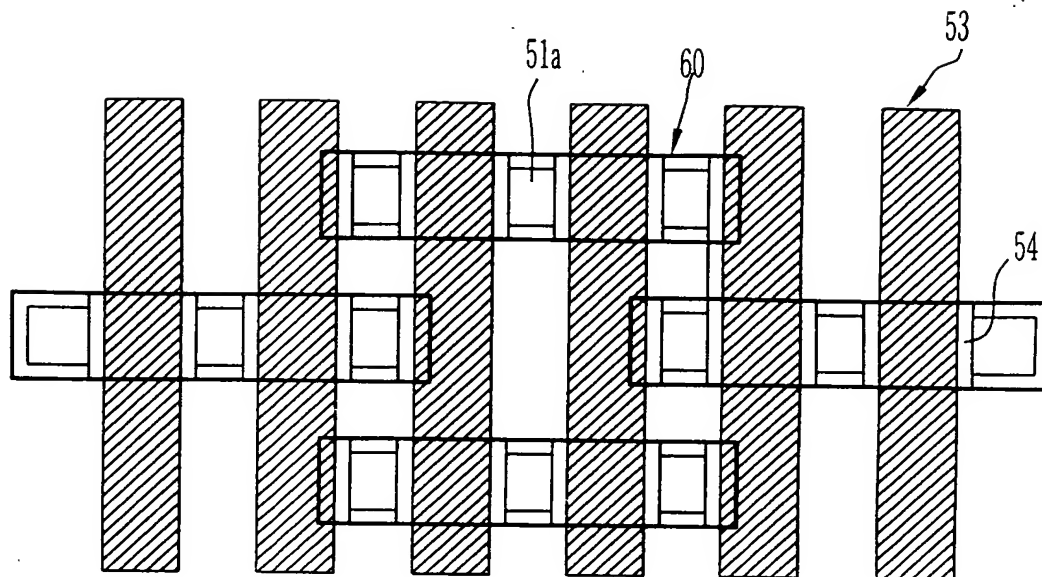
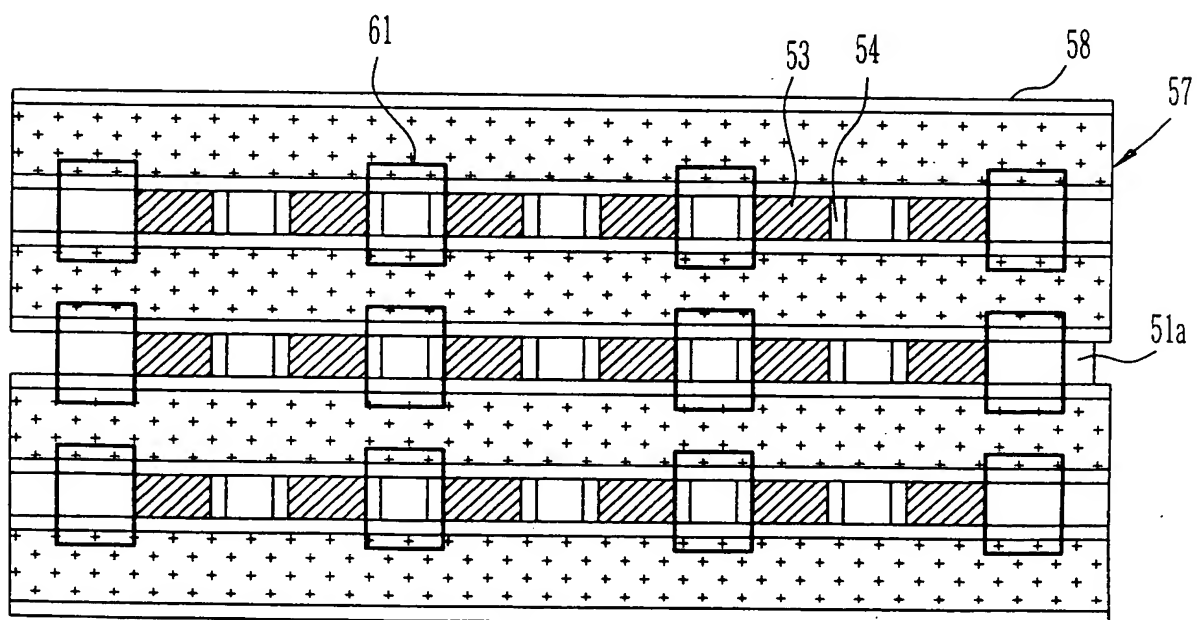


FIG. 5B



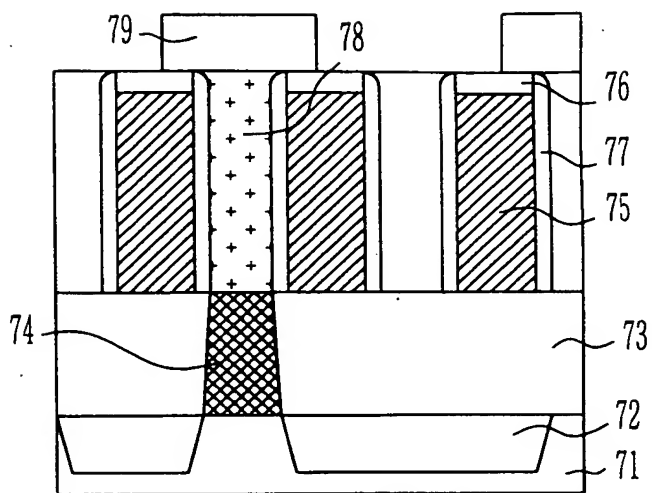


Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate (71) with a trench (72) and a central region (73) containing a cross-hatched pattern. A top layer (74) is formed on the substrate, and a central region (75) of the top layer contains '+' symbols. A thin layer (76) is formed on the top layer, and a thin layer (77) is formed on the central region (75). A thin layer (78) is formed on the top layer, and a thin layer (79) is formed on the central region (75).

